



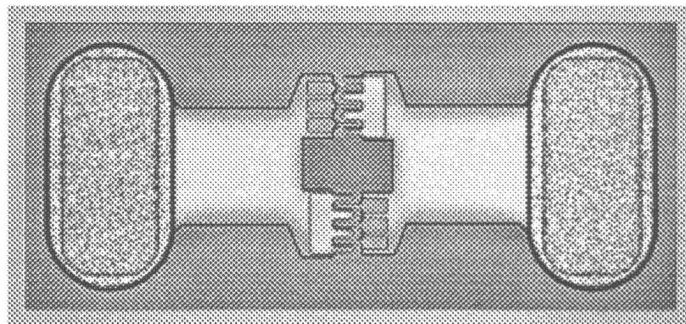
GaAs Schottky Diode Antiparallel Pair

Technical Data

HSCH-9551

Features

- **Low Junction Capacitance**— typically 40 fF
- **Low Series Resistance**— typically $3\ \Omega$
- **Large Bond Pads Suitable for Wire-bond or Flip-chip Assembly**
- **Polyimide Scratch Protection**



Description

The HSCH-9551 is an integrated antiparallel pair of GaAs Schottky barrier diodes. It is a beamless version of the HSCH-9251 antiparallel pair beam lead diode.

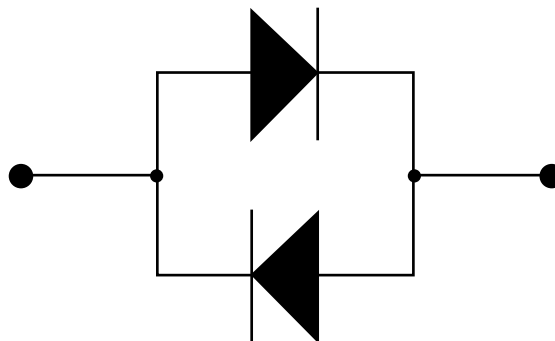
Chip Size:	620 x 325 μm (24.4 x 12.8 mils)
Chip Size Tolerance:	$\pm 10\ \mu\text{m}$ (± 0.4 mils)
Chip Thickness:	100 μm (4 mils)
Chip Thickness Tolerance:	$\pm 15\ \mu\text{m}$ (± 0.6 mils)
Bond Pad Sizes:	100 x 200 μm (3.9 x 7.9 mils)

Applications

The HSCH-9551 is a high-performance millimeter wave diode that can be used as a sub-harmonically pumped mixer or frequency multiplier in microwave and millimeter wave transceivers.

Specifications

- V_F (1 mA): 700-800 mV
- V_F (10 mA): 800-850 mV
- R_S (5 mA): $< 6\ \Omega$
- C_J (per diode): $< 0.050\ \text{pF}$





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This data sheet contains a variety of typical and guaranteed performance data. The information supplied should not be interpreted as a complete list of circuit specifications. In this data sheet the term *typical* refers to the 50th percentile performance. For additional information contact your local Agilent sales representative.

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Data subject to change.

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